

**Silicon NPN Power Transistors**

**BU2708DF**

**DESCRIPTION**

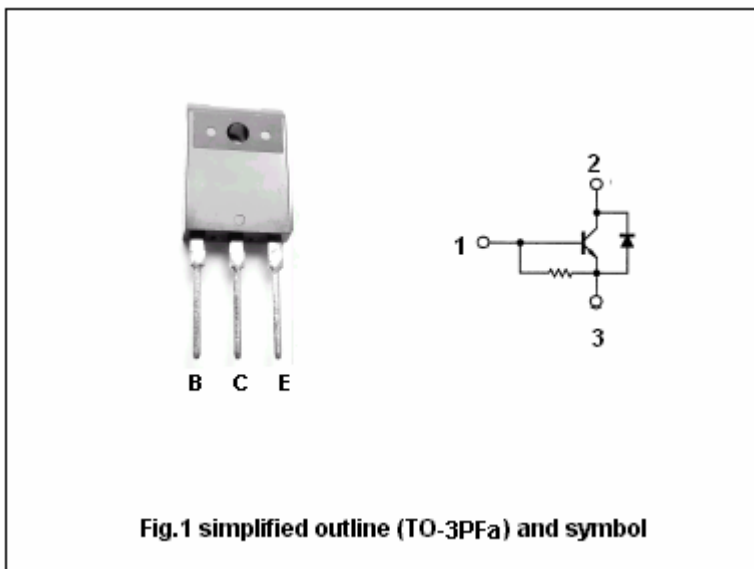
- With TO-3PFa package
- High voltage
- High speed switching
- Built-in damper diode

**APPLICATIONS**

- For use in horizontal deflection circuits of colour TV receivers.

**PINNING**

PIN	DESCRIPTION
1	Base
2	Collector
3	Emitter



**Absolute maximum ratings(Ta=25°C)**

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V <sub>CBO</sub>	Collector-base voltage	Open emitter	1700	V
V <sub>CEO</sub>	Collector-emitter voltage	Open base	825	V
I <sub>C</sub>	Collector current (DC)		8	A
I <sub>CM</sub>	Collector current -peak		15	A
I <sub>B</sub>	Base Collector current (DC)		4	A
I <sub>BM</sub>	Base current -peak		6	A
P <sub>tot</sub>	Total power dissipation	T <sub>C</sub> =25°C	45	W
T <sub>j</sub>	Junction temperature		150	°C
T <sub>stg</sub>	Storage temperature		-65~150	°C

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## CHARACTERISTICS

T<sub>j</sub>=25 °C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>(BR)EBO</sub>	Emitter-base breakdown voltage	I <sub>E</sub> =600mA ; I <sub>C</sub> =0	7.5	13.5		V
V <sub>CEsat</sub>	Collector-emitter saturation voltage	I <sub>C</sub> =4A ; I <sub>B</sub> =1.33 A			1.0	V
V <sub>BEsat</sub>	Base-emitter saturation voltage	I <sub>C</sub> =4A ; I <sub>B</sub> =1.33 A			1.0	V
I <sub>CES</sub>	Collector cut-off current	V <sub>CE</sub> =BV <sub>CEs</sub> ; V <sub>BE</sub> =0 T <sub>j</sub> =125 °C			1.0 2.0	mA
h <sub>FE-1</sub>	DC current gain	I <sub>C</sub> =1A ; V <sub>CE</sub> =5V		15		
h <sub>FE-2</sub>	DC current gain	I <sub>C</sub> =4A ; V <sub>CE</sub> =1V	3	6	7.3	
V <sub>F</sub>	Diode forward voltage	I <sub>F</sub> =4A		1.6		V

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PACKAGE OUTLINE

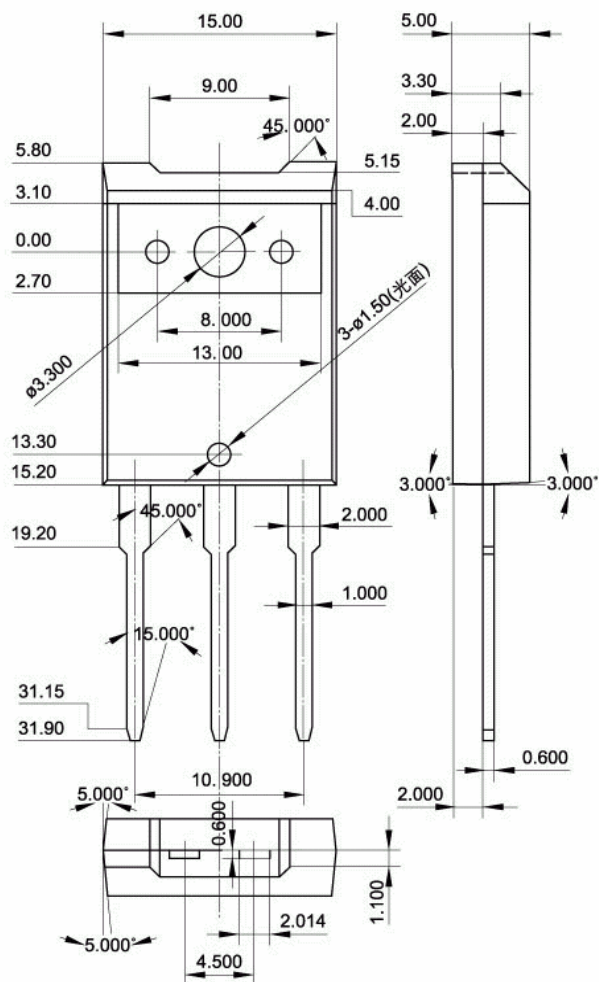


Fig.2 Outline dimensions (unindicated tolerance:±0.30mm)